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RoHS

COMPLIANT

HALOGEN

Thyristor Surface-Mount, Phase Control SCR, 16 A



D²PAK 2L (TO-263AB 2L)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
I _{T(AV)}	16 A						
V _{DRM} /V _{RRM}	1600 V						
V _{TM}	1.25 V						
I _{GT}	45 mA						
TJ	-40 °C to +125 °C						
Package	D ² PAK 2L (TO-263AB 2L)						
Circuit configuration	Single SCR						

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC[®]-JESD 47
- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS16S2L-M3 high voltage series of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	3.5	5.5						
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0						

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	16	٨						
I _{RMS}		25	A						
V _{RRM} /V _{DRM}		1600	V						
I _{TSM}		350	A						
V _T	16 A, T _J = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V		V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA						
VS-25TTS16SL-M3	1600	1600	10						

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1



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEO	VAL			
PARAMETER	STMBUL	163	CONDITIONS	TYP.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6	
Maximum RMS on-state current	I _{RMS}			2	25	А
Maximum peak, one-cycle,	L	10 ms sine pulse, r	ated V _{RRM} applied	3	00	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, r	no voltage reapplied	3	50	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, r	ated V _{RRM} applied	450		A ² s
Maximum - tior rusing	1-1	10 ms sine pulse, r	630		A-2	
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms	s, no voltage reapplied	6300		A²√s
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.25		V
On-state slope resistance	r _t	T _J = 125 °C		2.0	mΩ	
Threshold voltage	V _{T(TO)}	1j=125 C	1J = 125 C		.0	V
Maximum reverse and direct lookage average	1 /1	$T_J = 25 \ ^{\circ}C$		0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10		1
Holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C			00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max., linear$	to 80 %, $V_{DRM} = R_g - k = Open$	Open 500		V/µs
Maximum rate of rise of turned-on current	dl/dt			1:	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T_J = - 10 °C	60		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45	mA	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	2.0	.,	
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Deted volve	0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs				
Typical turn-off time	tq	1J = 125 C	110					

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VS-25TTS16S2L-M3

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS					
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W			
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/W			
Approximate weight			2	g			
Approximate weight			0.07	oz.			
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	25TT	S16S			

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

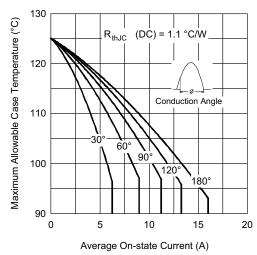
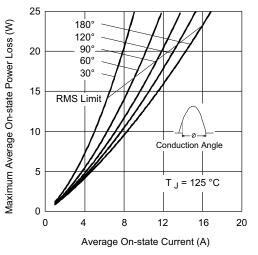
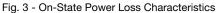
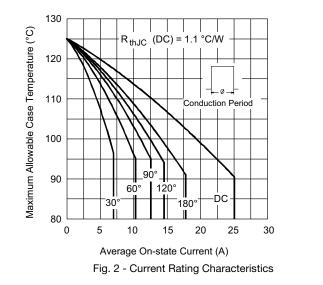
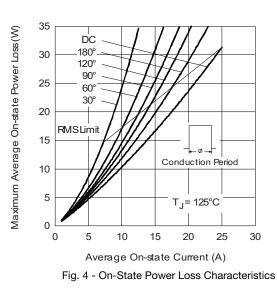


Fig. 1 - Current Rating Characteristics









Revision: 25-Sep-2024

3

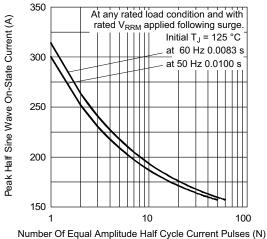
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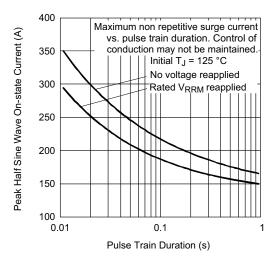


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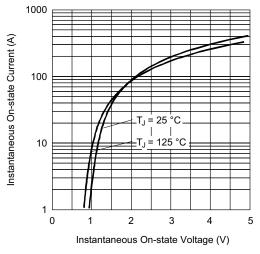




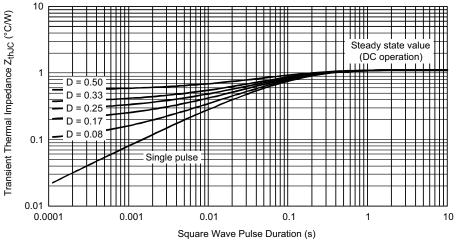














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 4
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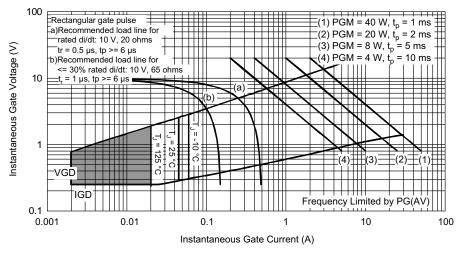


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

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ISHAY

Device code	VS-	25	т	т	S	16	S	2	L	-M3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)	(10)
	1 .	Visl	nay Sen	niconduo	ctors pro	oduct	Ŭ	Ŭ	Ŭ	U
	2 -	2 - Current rating (25 = 25 A)								
	3 -	 Circuit configuration: T = single thyristor 								
	4	Pac	Package: T = D ² PAK (TO-263AB)							
	5	Тур	e of silio	con:		: f :				
	6			rd recov ng: Volt	•		= V _{RRM}	л ———	- 16 = <i>1</i>	1600 V
	7 -	S =	surface	mounta	able					
	8 -	2 =	true 2 p	in D ² PA	K					
	9 -	L =	tape an	d reel (le	eft orien	ted), for	differe	nt orien	tation co	ontact fa
	10			ntal digit gen-free		-complia	ant, and	termina	ations le	ad (Pb)-

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS16S2L-M3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96683					
Part marking information	www.vishay.com/doc?96693					
Packaging information	www.vishay.com/doc?96317					

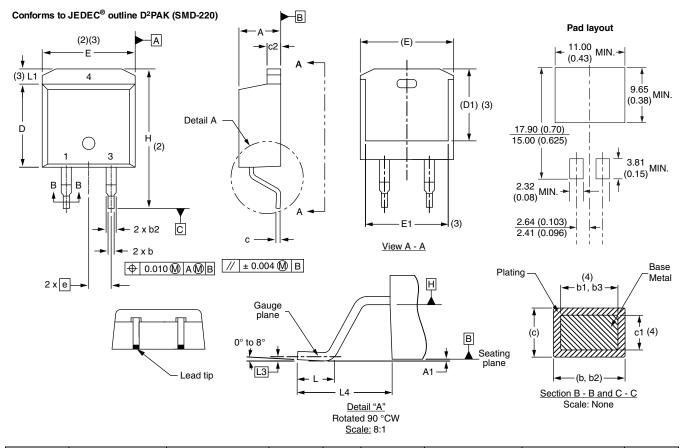
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D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES		NOTES				MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3		
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3		
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3		
b1	0.51	0.89	0.020	0.035	4		е	2.54 BSC		0.100 BSC				
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625			
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110			
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3		
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.010 BSC				
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208			
D	8.51	9.65	0.335	0.380	2									

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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1

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1